

FIG.1A

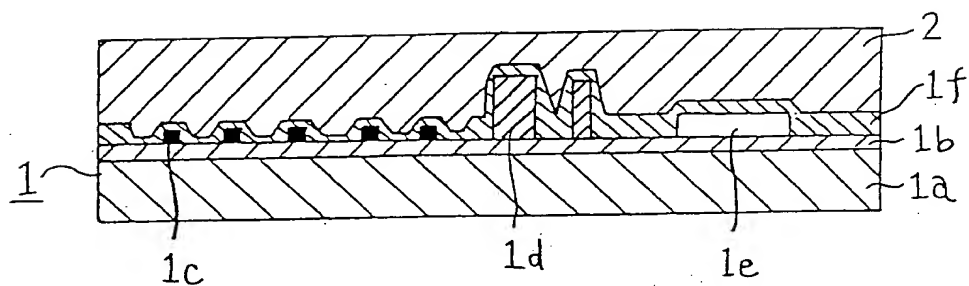


FIG.1B

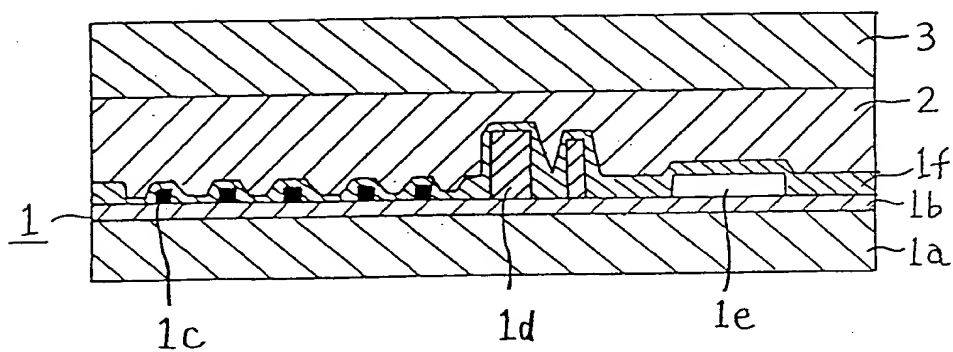


FIG.1C

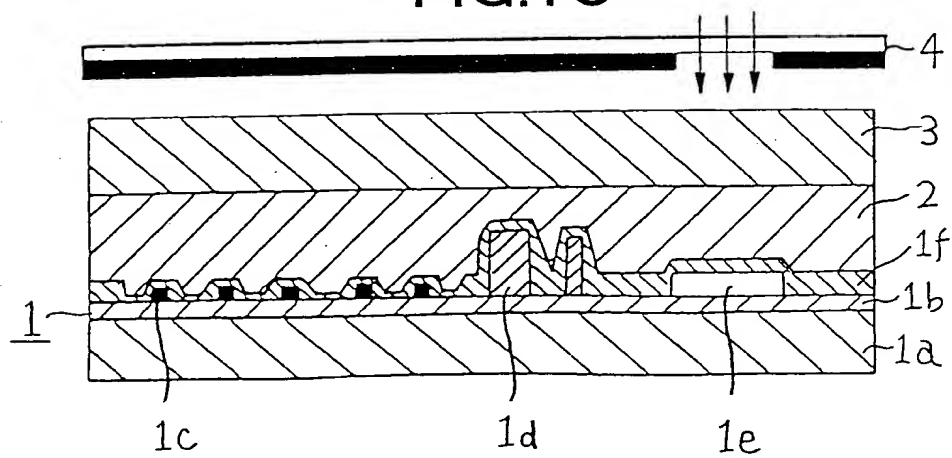


FIG.1D

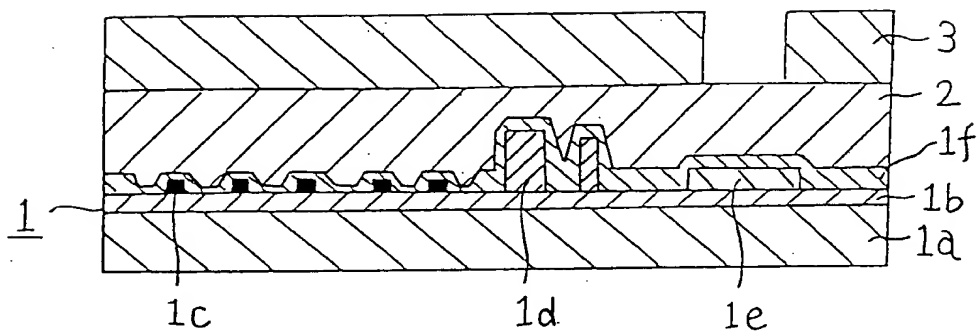


FIG.1E

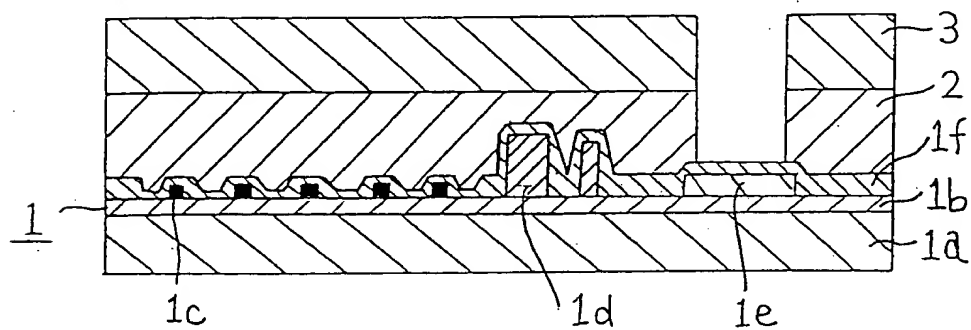


FIG.1F

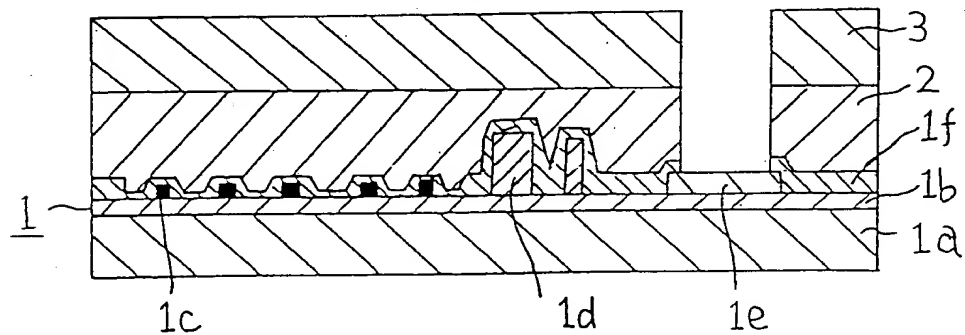
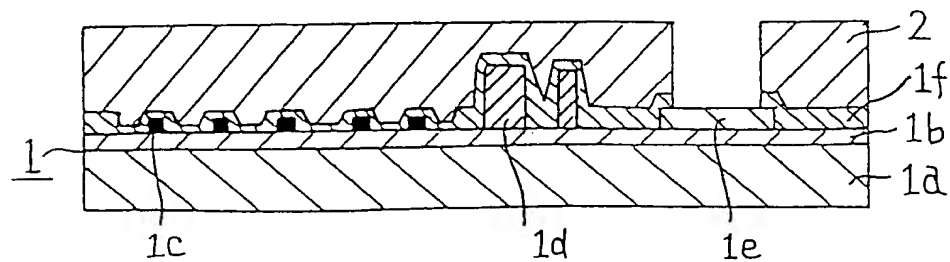


FIG.1G



A cross-sectional view of a semiconductor device. The device consists of a substrate 1a, a thin layer 1b, a patterned layer 1c, a central structure 1d, and a top layer 1f. A reference numeral 1 is shown on the left.



FIG.3A

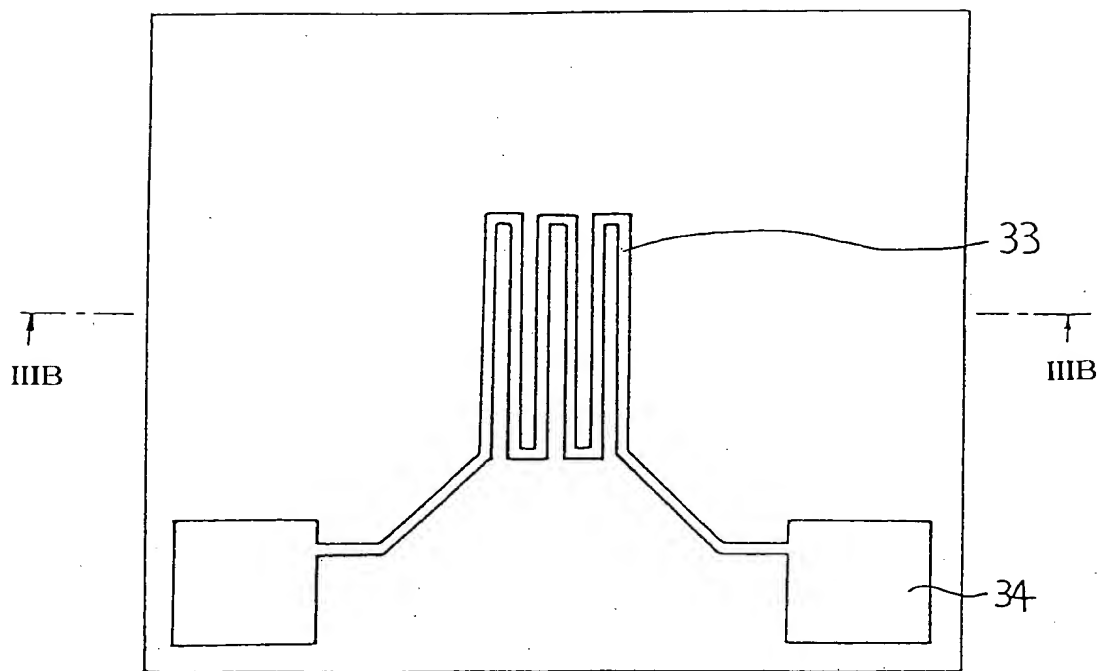


FIG.3B

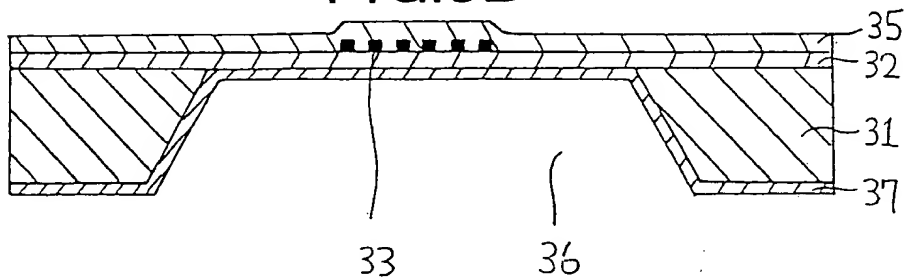




FIG.4A

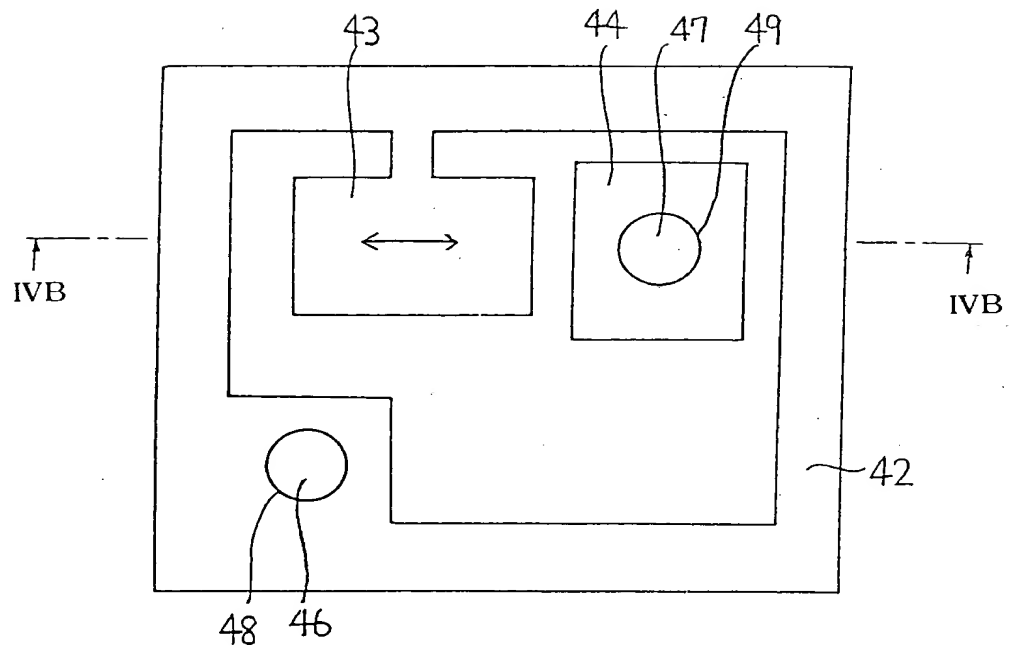


FIG.4B

